

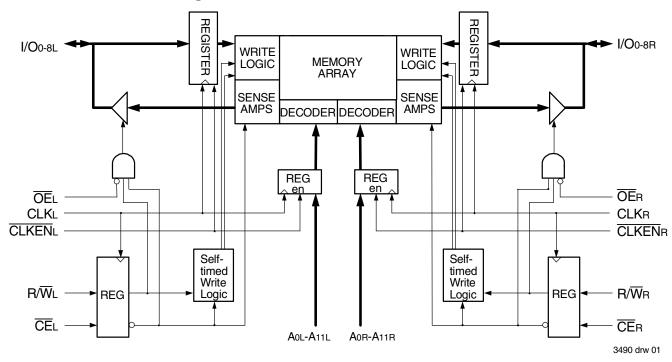
IDT70914S

Features

- High-speed clock-to-data output times
 - Military: 20/25ns (max.)
 - Commercial: 12/15/20ns (max.)
- Low-power operation
 - IDT70914S
 - Active: 850 mW (typ.) Standby: 50 mW (typ.)
 - Architecture based on D
- Architecture based on Dual-Port RAM cells
 - Allows full simultaneous access from both ports
- Synchronous operation
 - 4ns setup to clock, 1ns hold on all control, data, and address inputs
 - Data input, address, and control registers

- Fast 12ns clock to data out
- Self-timed write allows fast cycle times
- 16ns cycle times, 60MHz operation
- ◆ TTL-compatible, single 5V (± 10%) power supply
- Clock Enable feature
- Guaranteed data output hold times
- Available in 68-pin PLCC, and 80-pin TQFP
- Military product compliant to MIL-PRF-38535 QML
- Industrial temperature range (-40°C to +85°C) is available for selected speeds.
- Recommended for replacement of IDT7099 (4K x 9) if separate 9th bit data control signals are not required
- Green parts available, see ordering information

Functional Block Diagram



Description

The IDT70914 is a high-speed 4K x 9 bit synchronous Dual-Port RAM. The memory array is based on Dual-Port memory cells to allow simultaneous access from both ports. Registers on control, data, and address inputs provide low set-up and hold times. The timing latitude provided by this approach allow systems to be designed with very short cycle times. With an input data register, this device has been optimized for applications having unidirectional data flow or bi-directional data flow in bursts.

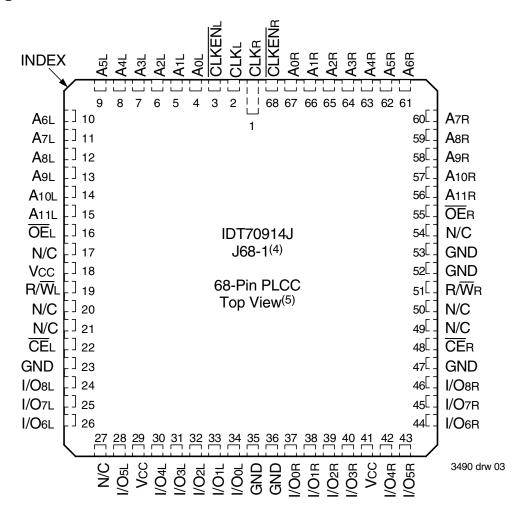
The IDT70914 utilizes a 9-bit wide data path to allow for parity at the user's option. This feature is especially useful in data communication applications where it is necessary to use a parity bit for transmission/

reception error checking.

Fabricated using IDT's CMOS high-performance technology, these Dual-Ports typically operate on only 850mW of power at maximum high-speed clock-to-data output times as fast as 12ns. An automatic power down feature, controlled by $\overline{\text{CE}}$, permits the on-chip circuitry of each port to enter a very low standby power mode.

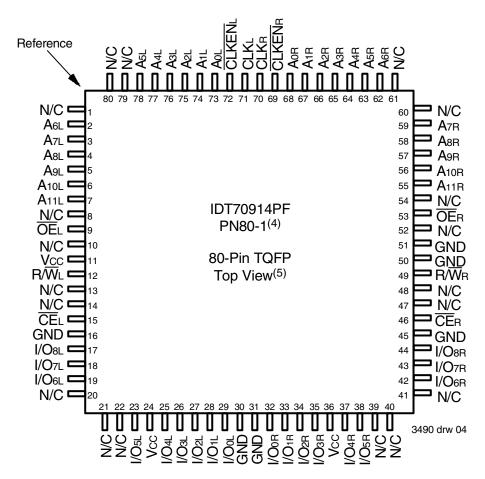
The IDT70914 is packaged in a 68-pin PLCC, and an 80-pin TQFP. Military grade product is manufactured in compliance with the latest revision of MIL-PRF-38535 QML, making it ideally suited for military temperature applications demanding the highest level of performance and reliability.

Pin Configurations (1,2,3)



- 1. All Vcc pins must be connected to power supply.
- 2. All ground pins must be connected to ground supply.
- 3. J68-1 package body is approximately .95 in x .95 in x .17 in.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

Pin Configuration^(1,2,3) (con't.)



- 1. All Vcc pins must be connected to power supply.
- 2. All ground pins must be connected to ground supply.
- 3. PN80-1 package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

Absolute Maximum Ratings(1)

Symbol	Rating	Commercial & Industrial	Military	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	٧
VTERM ⁽²⁾	Terminal Voltage	-0.5 to Vcc	-0.5 to Vcc	V
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	°C
Tstg	Storage Temperature	-65 to +150	-65 to +150	°C
Іоит	DC Output Current	50	50	mA

NOTES: 3490 tbl 01

- 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 10%.

Capacitance

(TA = +25°C, f = 1.0MHz) TQFP Only

Symbol	Parameter	Conditions	Max.	Unit
Cin	Input Capacitance	VIN = 3dV	8	pF
Соит	Output Capacitance	Vout = 3dV	9	pF

NOTES:

- 1. These parameters are determined by device characterization, but are not production tested.
- 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.

Maximum Operating Temperature and Supply Voltage^(1,2)

aria Sappi	voltage		
Grade	Ambient Temperature	GND	Vœ
Military	-55°C to+125°C	0V	5.0V <u>+</u> 10%
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

NOTES:

3490 tbl 02

- 1. This is the parameter TA. This is the "instant on" casae temperature.
- 2. Industrial temperature: for specific speeds, packages and powers contact your

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
VIH	Input High Voltage	2.2	_	6.0(2)	V
VIL	Input Low Voltage	-0.5 ⁽¹⁾		0.8	V

NOTES:

3490 tbl 03

- 1. $VIL \ge -1.5V$ for pulse width less than 10ns.

2. VTERM must not exceed Vcc + 10%.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ($Vcc = 5.0V \pm 10\%$)

			70914S		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Iu	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, Vin = 0V to Vcc	-	10	μA
ILO	Output Leakage Current	CE = VH, Vout = 0V to Vcc	_	10	μΑ
Vol	Output Low Voltage	loL = +4mA	_	0.4	V
Voh	Output High Voltage	IOH = -4mA	2.4	_	V

NOTE:

3490 tb105

1. At $Vcc \le 2.0V$, input leakages are undefined

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range $^{(4,5)}$ (Vcc = 5V ± 10%)

,		70914S12 70914S15 Com'l Only Com'l Only						
Symbol	Parameter	Test Condition	Version	Typ. ⁽²⁾	Max.	Typ. ⁽²⁾	Max.	Unit
lcc	Dynamic Operating Current	CEL and CER = VIL,	COM'L	190	310	180	300	mA
	(Both Ports Active)	Outputs Disabled f = fmax ⁽¹⁾	MIL & IND					
ISB1	Standby Current (Both Ports - TTL	CEL and CER = VH	COM'L	95	150	90	140	mA
	Level Inputs)	$f = f_{MAX}^{(1)}$	MIL & IND					
ISB2	Standby Current (One Port - TTL	$\overline{\overline{CE}}$ "A" = VIL and $\overline{\overline{CE}}$ "B" = VIH $^{(3)}$	COM'L	170	220	160	210	mA
	Level Inputs)	Active Port Outputs Disabled, f=fmax ⁽¹⁾	MIL & IND			-		
ISB3	Full Standby	Both Ports CER and	COM'L	10	15	10	15	mA
	Current (Both Ports - All CMOS Level Inputs)	$\overline{\text{CEL}}$ ≥ Vcc - 0.2V Vin ≥ Vcc - 0.2V or Vin ≤ 0.2V, f = 0 ⁽²⁾	MIL & IND	_	_		_	
ISB4	Full Standby Current (One Port - All CMOS	$\overline{CE}_{B''} = VCC - 0.2V^{(3)}$		165	210	155	200	mA
	Level Inputs)	$V_{IN} \ge \overline{V}_{CC}$ - 0.2V or $V_{IN} \le 0.2V$, Active Port Outputs Disabled $f = f_{IM} X^{(1)}$	MIL & IND					

3490 tbl 06a

				70914S20 Com'l & Military		70914S25 Military Only		
Symbol	Parameter	Test Condition	Version	Typ. ⁽²⁾	Max.	Typ. ⁽²⁾	Max.	Unit
lcc	Dynamic Operating Current	CEL and CER = VIL,	COM'L	170	290			mA
	(Both Ports Active)	Outputs Disabled f = fmax ⁽¹⁾	MIL & IND	170	310	160	290	
ISB1	Standby Current	CEL and CER = V⊪	COM'L	85	130	_	_	mA
	(Both Ports - TTL Level Inputs)	$f = f_{MAX}^{(1)}$	MIL & IND	85	140	80	130	
ISB2	Standby Current	CE"A" = VIL and	COM'L	150	200	_	_	mA
	(One Port - TTL Level Inputs)	CE'B" = V _{IH} (3) Active Port Outputs Disabled, f=fMax ⁽¹⁾	MIL & IND	150	210	140	200	
ISB3	Full Standby	Both Ports CER and	COM'L	10	15	_	_	mA
	Current (Both Ports - All CMOS Level Inputs)	$\overline{\text{CEL}} \ge \text{Vcc} - 0.2\text{V}$ $\text{Vin} \ge \text{Vcc} - 0.2\text{V}$ or $\text{Vin} \le 0.2\text{V}$, $f = 0^{(2)}$	MIL & IND	10	20	10	20	
ISB4	Full Standby $\overline{CE}^{A^*} \leq 0.2V$ and $\overline{CE}^{B^*} \geq Vcc - 0.2V^{(3)}$		COM'L	145	190		_	mA
	Port - All CMOS Level Inputs)	$V_{IN} \ge \overline{V}_{CC}$ - 0.2V or $V_{IN} \le 0.2V$, Active Port Outputs Disabled $f = f_{MAX}^{(1)}$	MIL & IND	145	200	135	190	

- 1. At fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcvc, using "AC TEST CONDITIONS" at input levels
- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. Vcc = 5V, TA = 25°C for Typ, and are not production tested. Icc pc = 150mA (Typ).
- 5. Industrial temperature: for specific speeds, packages and powers contact your sales office.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1,2 and 3

3490 tbl 07

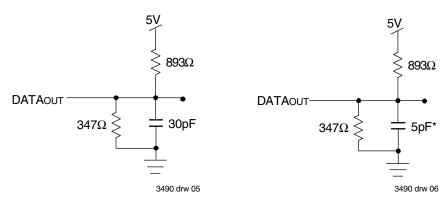


Figure 1. AC Output Test load.

Figure 2. Output Test Load (For tcklz, tckHz, tolz, and toHz). *Including scope and jig.

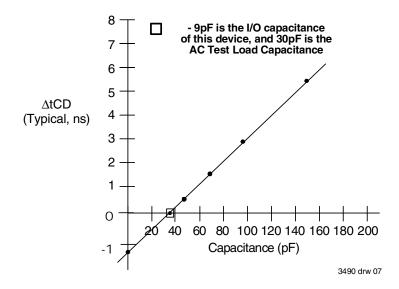


Figure 3. Typical Output Derating (Lumped Capacitive Load).

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)⁽³⁾ (Commercial: Vcc = 5V ± 10%, TA = 0°C to +70°C; Military: Vcc = 5V ± 10%, TA = -55°C to +125°C)

			4S12 I Only	70914S15 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
tcyc	Clock Cycle Time	16	_	20		ns
tсн	Clock High Time	6	_	6	_	ns
tcl	Clock Low Time	6	_	6	_	ns
tco	Clock High to Output Valid	_	12	_	15	ns
ts	Registered Signal Set-up Time	4	_	4	_	ns
tн	Registered Signal Hold Time	1	_	1	_	ns
toc	Data Output Hold After Clock High	3	_	3	_	ns
tcklz	Clock High to Output Low-Z ^(1,2)	2	_	2		ns
tckhz	Clock High to Output High-Z ^(1,2)	_	7	_	7	ns
toe	Output Enable to Output Valid	ı	7	_	8	ns
tolz	Output Enable to Output Low-Z ^(1,2)	0		0		ns
tonz	Output Disable to Output High-Z ^(1,2)	_	7	_	7	ns
tsck	Clock Enable, Disable Set-up Time	4	_	4		ns
thck	Clock Enable, Disable Hold Time	2	_	2		ns
ort-to-Port [Delay					
tcwdd	Write Port Clock High to Read Data Delay	_	25	_	30	ns
tcss	Clock-to-Clock Setup Time		13		15	ns

3490 tbl 08a

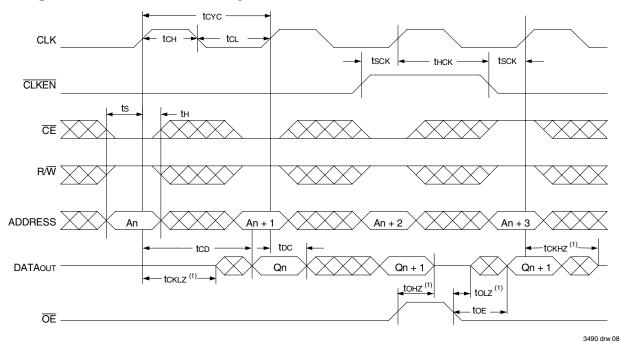
		70914S20 Com'l & Military		70914S25 Military Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
tcyc	Clock Cycle Time	20	_	25		ns
tсн	Clock High Time	8	_	10		ns
tcL	Clock Low Time	8	_	10		ns
tcp	Clock High to Output Valid		20		25	ns
ts	Registered Signal Set-up Time	5	_	6	_	ns
tн	Registered Signal Hold Time	1	_	1	_	ns
toc	Data Output Hold After Clock High	3	_	3		ns
tcklz	Clock High to Output Low-Z ^(1,2)	2	_	2		ns
tckhz	Clock High to Output High-Z ^(1,2)		9		12	ns
toe	Output Enable to Output Valid	_	10		12	ns
tolz	Output Enable to Output Low-Z ^(1,2)	0	_	0		ns
tonz	Output Disable to Output High-Z ^(1,2)		9		11	ns
tsck	Clock Enable, Disable Set-up Time	5	_	6		ns
thck	Clock Enable, Disable Hold Time	2	_	2	_	ns
Port-to-Port D	elay					
tcwdd	Write Port Clock High to Read Data Delay	_	35		45	ns
toss	Clock-to-Clock Setup Time		15		20	ns

NOTES:

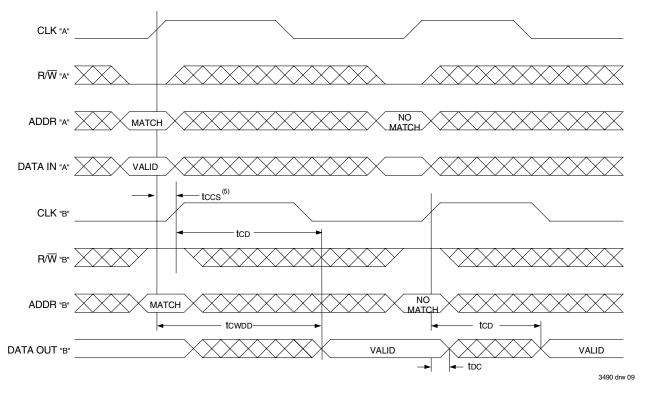
- 1. Transition is measured 0mV from Low or High impedance voltage with the Output Test Load (Figure 2).
- 2. This parameter is guaranteed by device characterization, but is not production tested.
- 3. Industrial temperature: for specific speeds, packages and powers contact your sales office.

3490 tbl 08b

Timing Waveform of Read Cycle, Either Side

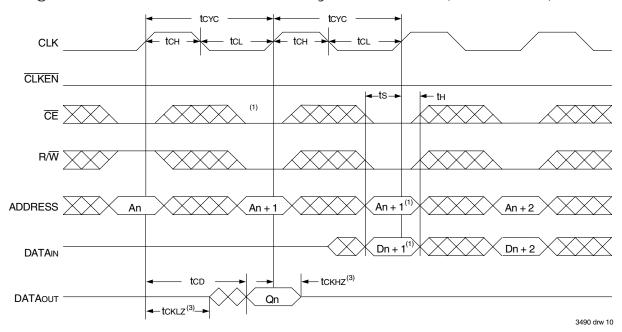


Timing Waveform of Write with Port-to-Port Read^(2,3,4)

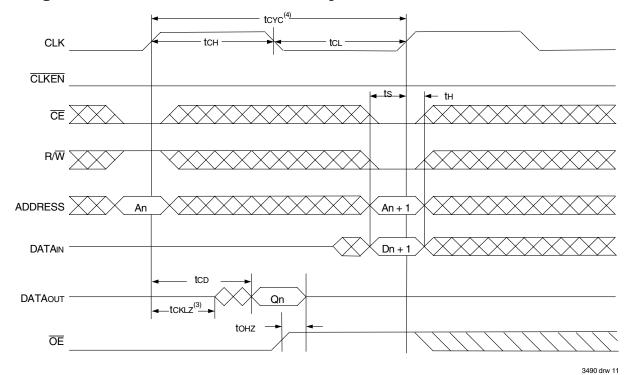


- 1. Transition is measured ±200mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. $\overline{CE}_L = \overline{CE}_R = V_{IL}$, $\overline{CLKEN}_L = \overline{CLKEN}_R = V_{IL}$.
- 3. $\overline{\text{OE}} = \text{V}_{\text{IL}}$ for the reading port, port 'B'.
- 4. All timing is the same for left and right ports. Ports "A" may be either the left or right port. Port "B" is opposite from port "A".
- 5. If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwbb. If tccs > maximum specified, then data from right port READ is not valid until tccs + tcb. tcwbb does not apply in this case.

Timing Waveform of Read-to-Write Cycle No. $1^{(1,2)}$ (tcyc = min.)



Timing Waveform of Read-to-Write Cycle No. 2⁽⁴⁾ (tcyc > min.)



- 1. For tcyc = min.; data out coincident with the rising edge of the subsequent write clock can occur. To ensure writing to the correct address location, the write must be repeated on the second write clock rising edge. If $\overline{CE} = V_{IL}$, invalid data will be written into array. The An+1 must be rewritten on the following cycle.
- 2. OE LOW throughout
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. For tcyc > min.; $\overline{\text{OE}}$ may be used to avoid data out coincident with the rising edge of the subsequent write clock. Use of $\overline{\text{OE}}$ will eliminate the need for the write to be repeated.

Functional Description

The IDT70914 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide very short set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal. An asynchronous output enable is provided to ease asynchronous bus interfacing.

The internal write pulse width is dependent on the LOW to HIGH

transitions of the clock signal allowing the shortest possible realized cycle times. Clock enable inputs are provided to stall the operation of the address and data input registers without introducing clock skew for very fast interleaved memory applications.

A HIGH on the $\overline{\text{CE}}$ input for one clock cycle will power down the internal circuitry to reduce static power consumption.

Truth Table I: Read/Write Control(1)

		Input	s	Outputs		
Sy	Synchronous ⁽³⁾		Asynchronous	·		
CLK	ΖĒ	R/W	▼		Mode	
1	Н	Χ	Х	High-Z	Deselected, Power-Down	
1	L	L	Х	DATAIN	Selected and Write Enabled	
1	L	Н	L	DATA out	Read Selected and Data Output Enable Read	
1	Х	Χ	Н	High-Z	Outputs Disabled	

3490 tbl 09

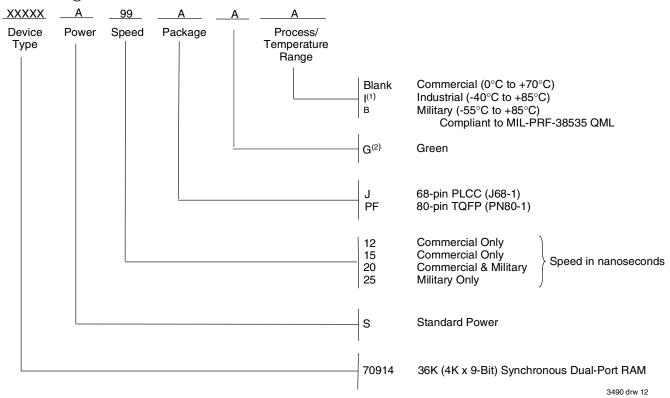
Truth Table II: Clock Enable Function Table⁽¹⁾

	Inputs		Inputs Register Inputs		Register Outputs ⁽⁴⁾	
Mode	CLK ⁽³⁾	CLKEN ⁽²⁾	ADDR	DATAIN	ADDR	DATAOUT
Load "1"	1	L	Н	Н	Н	Н
Load "0"	1	L	L	L	L	L
Hold (do nothing)	1	Н	Х	Х	NC	NC
, ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	Х	Н	Х	Х	NC	NC

NOTES: 3490 tbl 10

- 1. 'H' = HIGH voltage level steady state, 'h' = HIGH voltage level one set-up time prior to the LOW-to-HIGH clock transition, 'L' = LOW voltage level steady state 'l' = LOW voltage level one set-up time prior to the LOW-to-HIGH clock transition, 'X' = Don't care, 'NC' = No change
- 2. CLKEN = VIL must be clocked in during Power-Up.
- 3. Control signals are initialted and terminated on the rising edge of the CLK, depending on their input level. When R/W and CE are LOW, a write cycle is initiated on the LOW-to-HIGH transition of the CLK. Termination of a write cycle is done on the next LOW-to-HIGH transistion of the CLK.
- 4. The register outputs are internal signals from the register inputs being clocked in or disabled by CLKEN.

Ordering Information



NOTE:

- 1. Industrial temperature range is available on selected TQFP packages in standard power. For specific speeds, packages and powers contact your sales office.
- 2. Green parts available. For specific speeds, packages and powers contact your sales office.

Datasheet Document History

3/10/99: Initiated datasheet document history

Converted to new format

Cosmetic and typographical corrections

Page 2 and 3 Added additional notes to pin configurations

6/7/99: Changed drawing format 11/10/99: Replaced IDT logo

5/24/00: Page 4 Increased storage temperature parameter

Clarified Taparameter

Page 5 DC Electrical parameters-changed wording from "open" to "disabled"

Changed ±200mV to 0mV in notes

1/12/01: Removed PGA pinout (obsolete package)

Changed cycle time of 12ns part from 17ns (58MHz) to 16ns (60MHz)

10/21/08: Page 11 Removed "IDT" from orderable part number 05/24/10: Page 1 Added green parts availability to features Page 11 Added green indicator to ordering information



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